# 2SC5841

### Silicon NPN epitaxial planar type

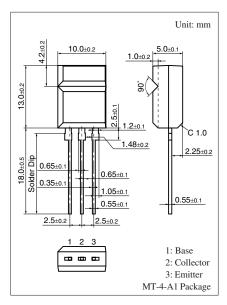
Power supply for Audio & Visual equipments such as TVs and VCRs Industrial equipments such as DC-DC converters

#### ■ Features

- $\bullet$  High-speed switching ( $t_{stg}$ : storage time/ $t_f$ : fall time is short)
- ullet Low collector-emitter saturation voltage  $V_{CE(sat)}$
- $\bullet$  Superior forward current transfer ratio  $h_{\text{FE}}$  linearity
- Allowing supply with the radial taping (MT-4)

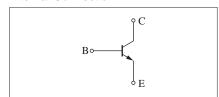
#### ■ Absolute Maximum Ratings $T_C = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)		$V_{CBO}$	80	V
Collector-emitter voltage (Base open)		V <sub>CEO</sub>	80	V
Emitter-base voltage (Collector open)		V <sub>EBO</sub>	5	V
Collector current		$I_C$	3	A
Peak collector current		$I_{CP}$	5	A
Collector power	$T_C = 25^{\circ}C$	P <sub>C</sub>	15	W
dissipation	$T_a = 25$ °C		2	
Junction temperature		$T_{j}$	150	°C
Storage temperature		T <sub>stg</sub>	-55 to +150	°C



Marking Symbol: C5841

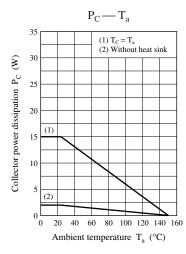
#### Internal Connection

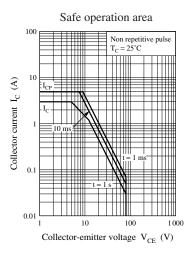


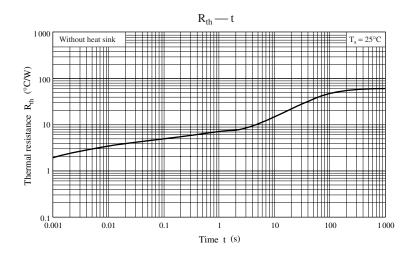
### ■ Electrical Characteristics $T_C = 25$ ° $C \pm 3$ °C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_C = 10 \text{ mA}, I_B = 0$	80			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 80 \text{ V}, I_{E} = 0$			100	μΑ
Collector-emitter cutoff current (Base open)	$I_{CEO}$	$V_{CE} = 80 \text{ V}, I_{B} = 0$			100	μΑ
Forward current transfer ratio	h <sub>FE1</sub>	$V_{CE} = 4 \text{ V}, I_{C} = 0.2 \text{ A}$	50			_
	h <sub>FE2</sub>	$V_{CE} = 4 \text{ V}, I_{C} = 1 \text{ A}$	80		280	
	h <sub>FE3</sub>	$V_{CE} = 4 \text{ V}, I_{C} = 3 \text{ A}$	20			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C = 3 \text{ A}, I_B = 375 \text{ mA}$			0.7	V
Transition frequency	$f_T$	$V_{CE} = 10 \text{ V}, I_{C} = 0.1 \text{ A}, f = 10 \text{ MHz}$		100		MHz
Turn-on time	t <sub>on</sub>	I <sub>C</sub> = 1 A, Resistance loaded		0.2		μs
Storage time	t <sub>stg</sub>	$I_{B1} = 0.1 \text{ A}, I_{B2} = -0.1 \text{ A}$		0.9		μs
Fall time	$t_{\rm f}$	$V_{CC} = 50 \text{ V}$		0.15		μs

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.







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